ON Semiconductor

Product Bulletin

Document # : PB20958X
Issue Date: 2 July 2015

Title of Change:	Die Datasheet correction for the AR1335
Effective date:	2 July 2015
Contact information:	Contact your local ON Semiconductor Sales Office or <Samuel.Shen@onsemi.com>
Type of notification:	ON Semiconductor will consider this change accepted.
Change category:	☐ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☒ Other ____________

Change Sub-Category(s):

☐ Manufacturing Site Change/Addition
☐ Manufacturing Process Change
☐ Material Change
☐ Product specific change
☒ Datasheet/Product Doc change
☐ Shipping/Packaging/Marking
☐ Other: ______________________

Sites Affected:

☒ All site(s) ☐ not applicable ☐ ON Semiconductor site(s) : ☐ External Foundry/Subcon site(s)

Description and Purpose:

It was identified by marketing that the Ordering information and Physical specifications table, and Reconstructed Wafer figures in the document revision B from May 2015 needed to be updated to include a 150 µm die thickness. In order to correct this, the following changes have been made.

Old Section:	**Updated Section:**
Order Information AR1335CSSC32SMD20	**Order Information** AR1335CSSC32SMD20 200µm AR1335CSSC32SMD10 150µm

Old Table 3:

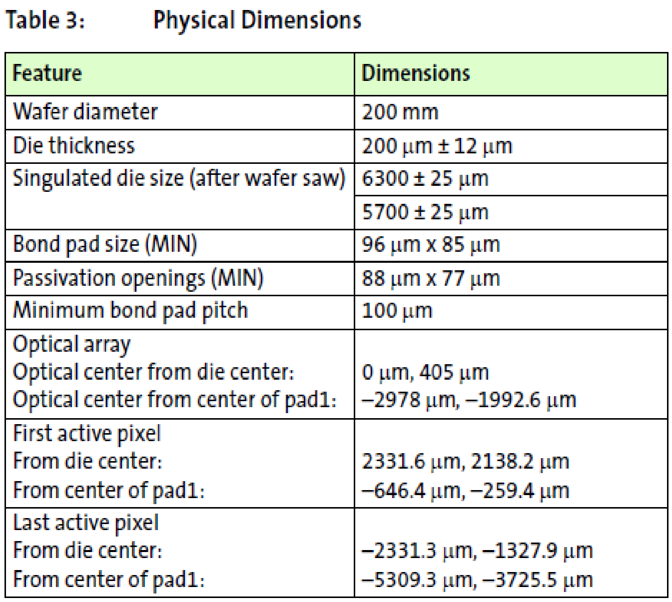


Table 3: Physical Dimensions

Feature	Dimensions
Wafer diameter	200 mm
Die thickness	200 µm ± 12 µm
Singulated die size (after wafer saw)	6300 ± 25 µm
	5700 ± 25 µm
Bond pad size (MIN)	96 µm x 85 µm
Passivation openings (MIN)	88 µm x 77 µm
Minimum bond pad pitch	100 µm
Optical array Optical center from die center: Optical center from center of pad1:	0 µm, 405 µm –2978 µm, –1992.6 µm
First active pixel From die center: From center of pad1:	2331.6 µm, 2138.2 µm –646.4 µm, –259.4 µm
Last active pixel From die center: From center of pad1:	–2331.3 µm, –1327.9 µm –5309.3 µm, –3725.5 µm

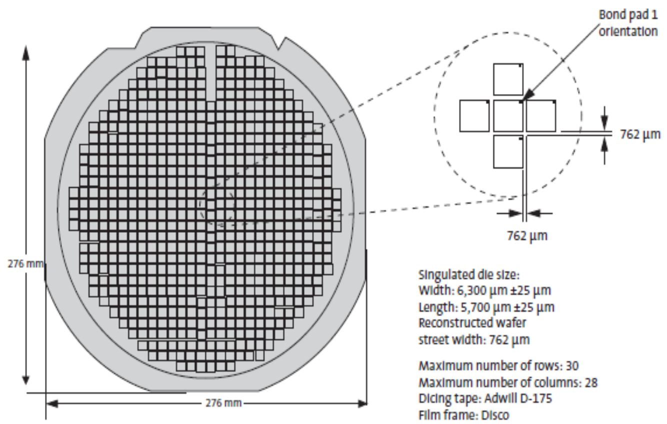
Updated Table 3:

Table 3: Physical Dimensions

Feature	Dimensions
Wafer diameter	200 mm
Die thickness	200 µm ± 12 µm, 150 µm ± 12 µm
Singulated die size (after wafer saw)	6300 ± 25 µm
	5700 ± 25 µm
Bond pad size (MIN)	96 µm x 85 µm
Passivation openings (MIN)	88 µm x 77 µm
Minimum bond pad pitch	100 µm
Optical array Optical center from die center: Optical center from center of pad1:	0 µm, 405 µm –2978 µm, –1992.6 µm
First active pixel From die center: From center of pad1:	2331.6 µm, 2138.2 µm –646.4 µm, –259.4 µm
Last active pixel From die center: From center of pad1:	–2331.3 µm, –1327.9 µm –5309.3 µm, –3725.5 µm

Old Figure 3:

Figure 3: Die Orientation in Reconstructed Wafer



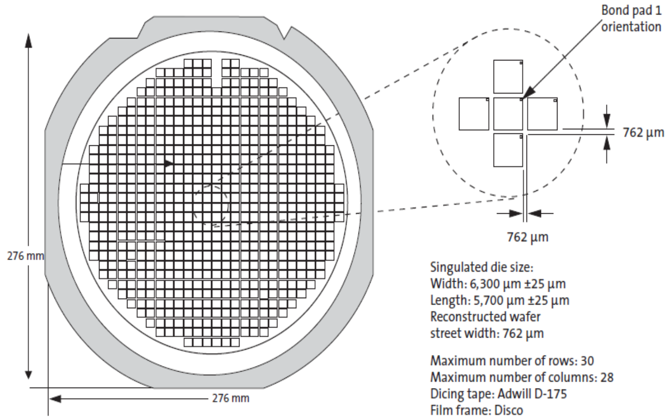
Singulated die size:
Width: 6,300 µm ±25 µm
Length: 5,700 µm ±25 µm
Reconstructed wafer
street width: 762 µm

Maximum number of rows: 30
Maximum number of columns: 28
Dicing tape: Adwill D-175
Film frame: Disco

Maximum total die count: 627

Updated Figure 3:

Figure 3: Die Orientation in Reconstructed Wafer, 150 µm



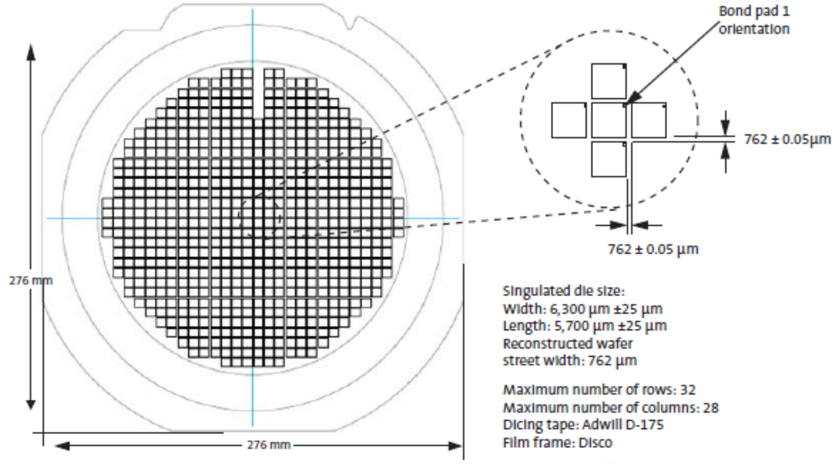
Singulated die size:
Width: 6,300 µm ±25 µm
Length: 5,700 µm ±25 µm
Reconstructed wafer
street width: 762 µm

Maximum number of rows: 30
Maximum number of columns: 28
Dicing tape: Adwill D-175
Film frame: Disco

Maximum total die count: 629

Added Figure 4:

Figure 4: Die Orientation in Reconstructed Wafer, 200 µm



Singulated die size:
Width: 6,300 µm ±25 µm
Length: 5,700 µm ±25 µm
Reconstructed wafer
street width: 762 µm

Maximum number of rows: 32
Maximum number of columns: 28
Dicing tape: Adwill D-175
Film frame: Disco

Maximum total die count: 627

These changes are the result of a documentation error only; there is no change to the product form, fit, or function.

List of affected Standard Parts:

AR1335CSSC32SMD20
AR1335CSSC32SMD10